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Vishay Semiconductor/Diodes Division
VS-ST380CH04C0

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sales@integrated-circuit.com

Phase Control Thyristors (Hockey PUK Version), 960 A

TO-200AB (E-PUK)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (E-PUK)
- Extended temperature range
- Low profile hockey PUK to increase current-carrying capability
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

Pb-free
RoHS COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY	
Package	TO-200AB (E-PUK)
Diode variation	Single SCR
$I_{T(AV)}$	960 A
V_{DRM}/V_{RRM}	400 V, 600 V
V_{TM}	1.58 V
I_{GT}	100 mA
T_J	-40 °C to 150 °C

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		960	A
	T_{hs}	80	°C
$I_{T(RMS)}$		2220	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	12 500	A
	60 Hz	13 000	
I^2t	50 Hz	782	kA^2s
	60 Hz	713	
V_{DRM}/V_{RRM}		400 to 600	V
t_q	Typical	100	µs
T_J		-40 to 150	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS				
TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM}, MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM}, MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST380CH..C	04	400	500	100
	06	600	700	

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current at heatsink temperature	$I_{T(AV)}$	180° conduction, half sine wave double side (single side) cooled			960 (440)	A
					80 (110)	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 25 °C heatsink temperature double side cooled			2220	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial $T_J = T_J$ maximum	12 500	
		t = 8.3 ms			13 000	
		t = 10 ms	100 % V_{RRM} reapplied		10 500	
		t = 8.3 ms			11 000	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reapplied		782	kA^2s
		t = 8.3 ms			713	
		t = 10 ms	100 % V_{RRM} reapplied		553	
		t = 8.3 ms			505	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied			7820	$kA^2\sqrt{s}$
Low level value of threshold voltage	$V_{T(TO)1}$	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.85	V
High level value of threshold voltage	$V_{T(TO)2}$	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.88	
Low level value of on-state slope resistance	r_{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.25	mΩ
High level value of on-state slope resistance	r_{t2}	(I > π x $I_{T(AV)}$), $T_J = T_J$ maximum			0.24	
Maximum on-state voltage	V_{TM}	I_{pk} = 2900 A, $T_J = T_J$ maximum, t_p = 10 ms sine pulse			1.58	V
Maximum holding current	I_H	T_J = 25 °C, anode supply 12 V resistive load			600	mA
Typical latching current	I_L				1000	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ µs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/µs
Typical delay time	t_d	Gate current 1 A, dI_g/dt = 1 A/µs V_d = 0.67 % V_{DRM}, T_J = 25 °C	1.0	µs
Typical turn-off time	t_q	I_{TM} = 550 A, $T_J = T_J$ maximum, dI/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 Ω, t_p = 500 µs	100	

BLOCKING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES TYP.	VALUES MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		10.0		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, f = 50 Hz, d% = 50		2.0		W
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		3.0		A
Maximum peak positive gate voltage	$+ V_{GM}$	$T_J = T_J$ maximum, $t_p \le 5$ ms		20		V
Maximum peak negative gate voltage	$- V_{GM}$			5.0		V
DC gate current required to trigger	I_{GT}	T_J = -40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	200	-	mA
		T_J = 25 °C		100	200	mA
		T_J = 150 °C		40	-	mA
DC gate voltage required to trigger	V_{GT}	T_J = -40 °C		2.5	-	V
		T_J = 25 °C		1.8	3.0	V
		T_J = 150 °C		1.0	-	V
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	10		mA
DC gate voltage not to trigger	V_{GD}			0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	T_J		-40 to 150	°C
Maximum storage temperature range	T_{Stg}			
Maximum thermal resistance, junction to heatsink	$R_{thJ\text{-}hs}$	DC operation single side cooled	0.09	K/W
		DC operation double side cooled	0.04	K/W
Maximum thermal resistance, case to heatsink	$R_{thC\text{-}hs}$	DC operation single side cooled	0.02	K/W
		DC operation double side cooled	0.01	K/W
Mounting force, ± 10 %			9800 (1000)	N (kg)
Approximate weight			83	g
Case style		See dimensions - link at the end of datasheet	TO-200AB (E-PUK)	

$\Delta R_{thJ\text{-}hs}$ CONDUCTION

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.010	0.011	0.007	0.007	$T_J = T_J$ maximum	K/W
120°	0.012	0.012	0.012	0.013		
90°	0.015	0.015	0.016	0.017		
60°	0.022	0.022	0.023	0.023		
30°	0.036	0.036	0.036	0.037		

Note

- The table above shows the increment of thermal resistance $R_{thJ\text{-}hs}$ when devices operate at different conduction angles than DC

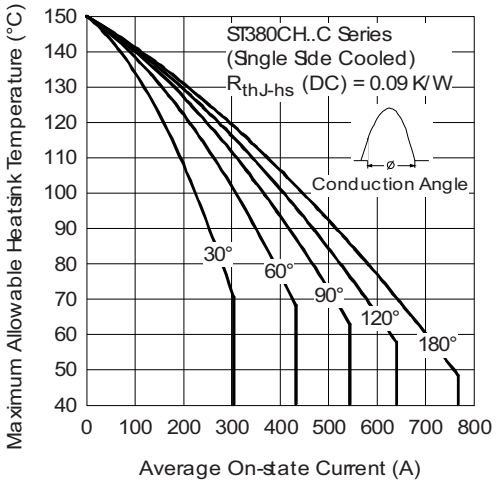


Fig. 1 - Current Ratings Characteristics

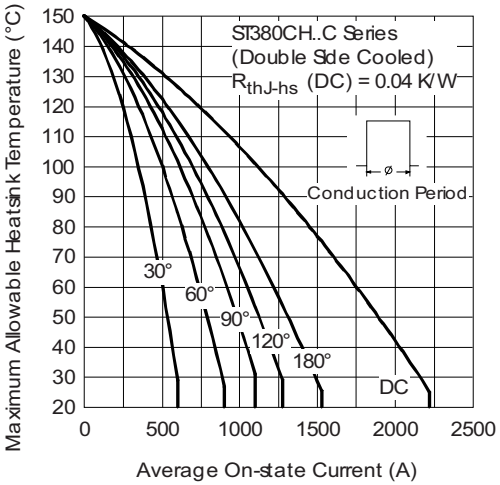


Fig. 4 - Current Ratings Characteristics

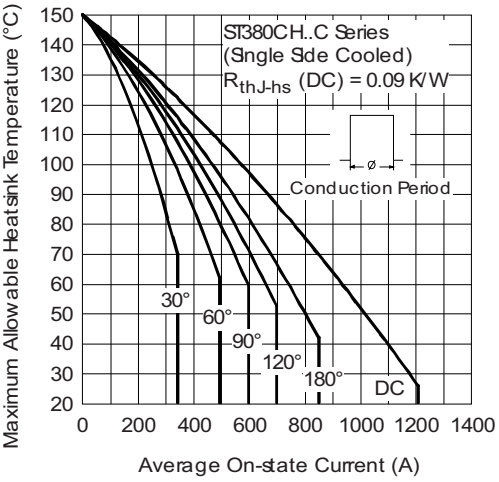


Fig. 2 - Current Ratings Characteristics

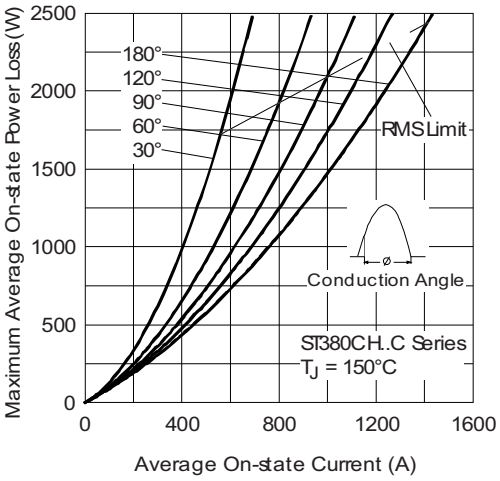


Fig. 5 - On-State Power Loss Characteristics

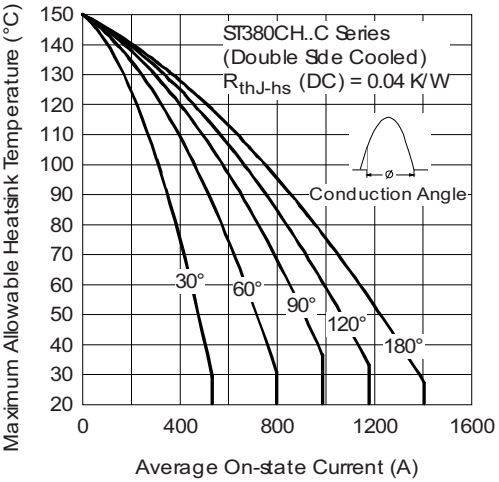


Fig. 3 - Current Ratings Characteristics

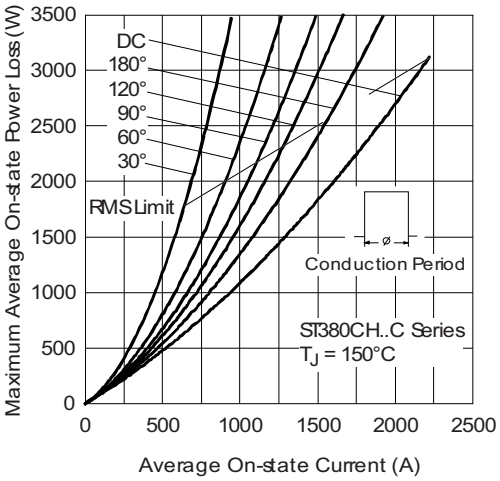


Fig. 6 - On-State Power Loss Characteristics

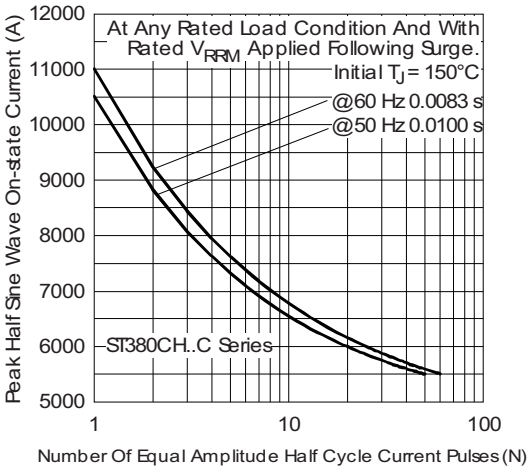


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

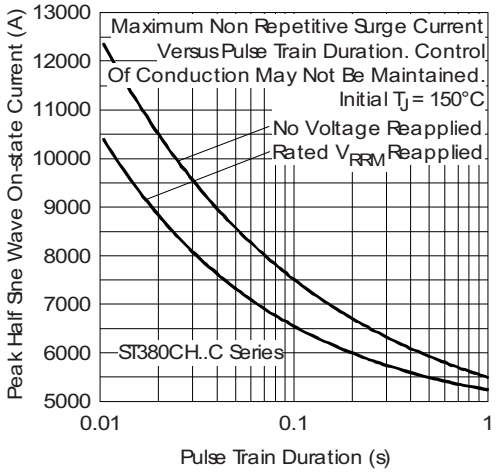


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

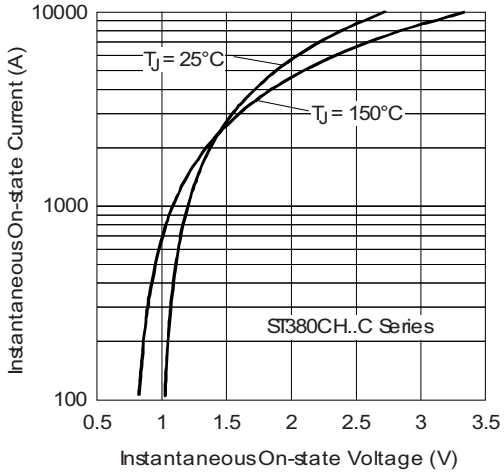


Fig. 9 - On-State Voltage Drop Characteristics

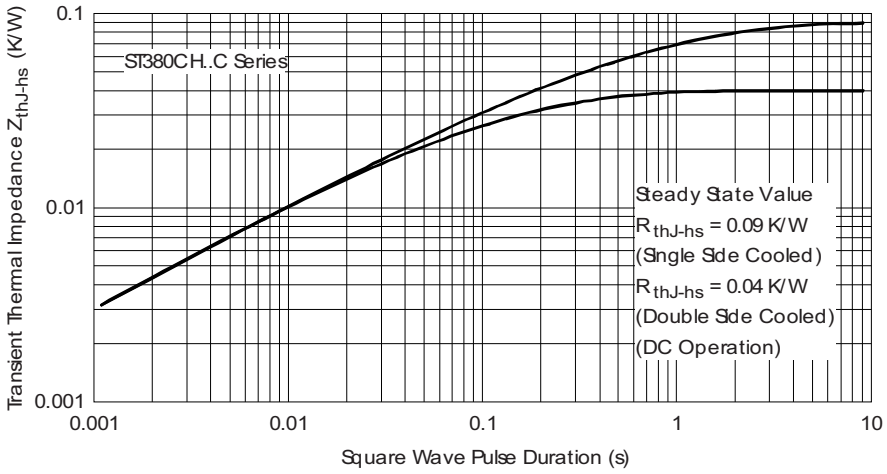


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

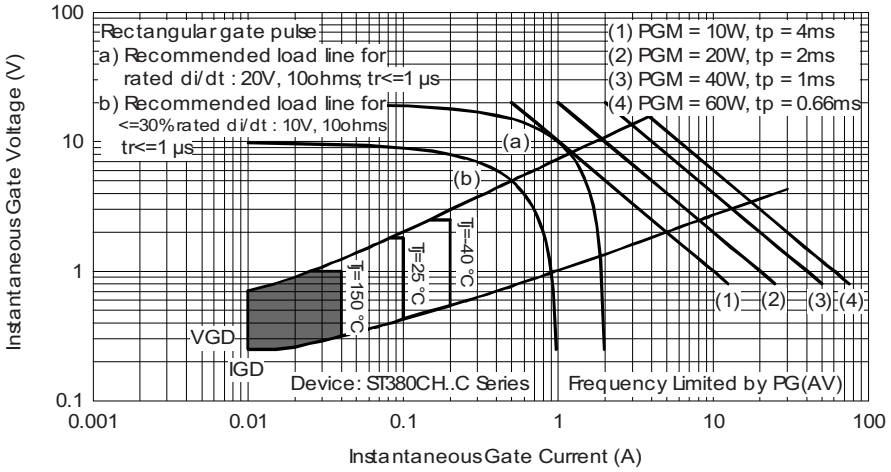


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

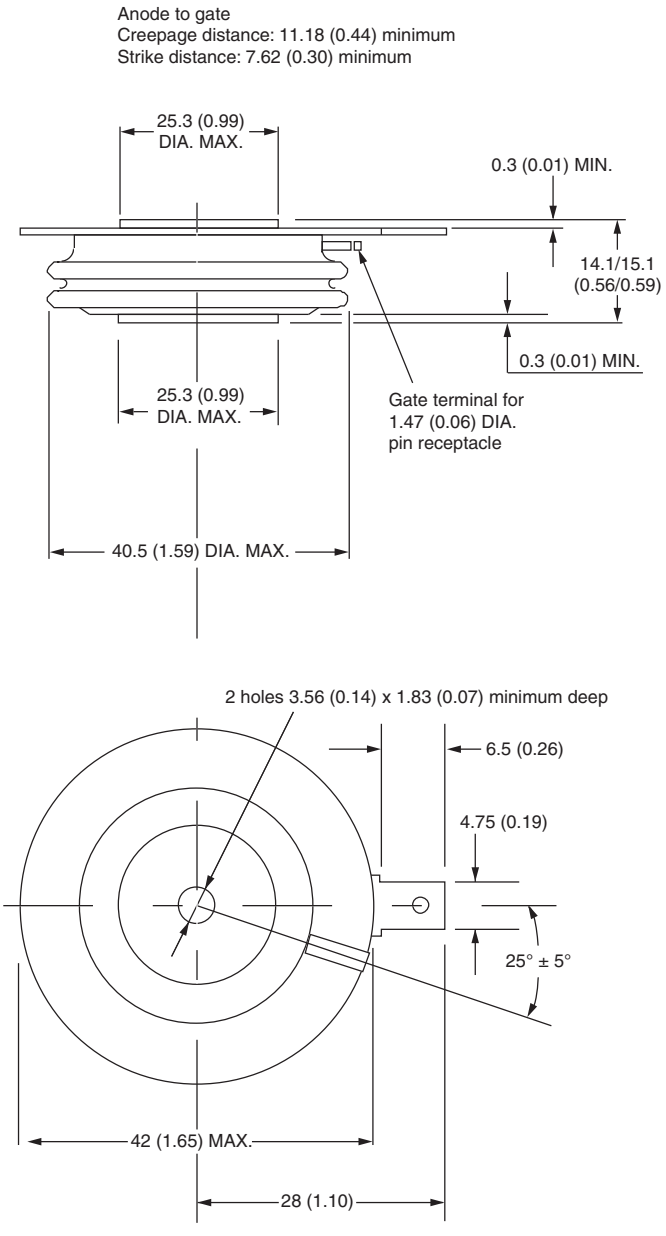
VS-	ST	38	0	CH	06	C	1	-
1	2	3	4	5	6	7	8	9

- **1** - Vishay Semiconductors product
- **2** - Thyristor
- **3** - Essential part number
- **4** - 0 = Converter grade
- **5** - CH = Ceramic PUK, high temperature
- **6** - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- **7** - C = PUK case TO-200AB (E-PUK)
- **8** - 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
  1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
  2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
  3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- **9** - Critical dV/dt: • None = 500 V/µs (standard selection)
  • L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95075

TO-200AB (E-PUK)

DIMENSIONS in millimeters (inches)



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)

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